

	Hits	Search Text	DBs
21	80	((reduc\$4 or decreas\$3 or eliminat\$4 or prevent\$4 or avoid\$4) same (photoresist or resist) same (poison\$3 or contaminat\$4 or decomposing or decomposition)) and (plasma same (treat\$4 or react\$4 or bombard\$4 or imping\$4) same (pre\$4clean\$4 or etch\$4 or remov\$4 or eliminat\$4) same ((native near9 oxide) or oxide or nitride or oxy\$3nitride) same (substrate or wafer or workpiece) same (DARC or underl\$5 or underlying or ((dielectric or inorganic or silicon or Si or SiON or silicon\$3nitride or Si\$2N\$2) near9 (ARC or anti\$3reflect\$3 or BARC or DARC))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
22	38	((reduc\$4 or decreas\$3 or eliminat\$4 or prevent\$4 or avoid\$4) same (photoresist or resist) same (poison\$3 or contaminat\$4 or decompos\$4) same plasma same (treat\$4 or react\$4 or bombard\$4 or imping\$4) same (pre\$4clean\$4 or etch\$4 or remov\$4 or eliminat\$4) same ((native near9 oxide) or oxide or nitride or oxy\$3nitride) same (substrate or wafer or workpiece)) and ((substrate or wafer or platen) same (DARC or (bottom near9 layer) or underlying or ((dielectric or inorganic or silicon or Si or SiON or silicon\$3nitride or Si\$2N\$2) near22 (ARC or anti\$3reflect\$3 or BARC or DARC))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB